# STUDYING THE DECAY KINETICS OF AN OXYGEN SOLID SOLUTION IN Cz-Si SPECIMENS AT THEIR SQUEEZING

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S u m m a r y

Three-crystal X-ray diffractometry (TCD) was used to study the decay kinetics of an oxygen solid solution in silicon crystals grown by the Czochralski method (Cz–Si) and subjected to squeezing. The squeezing stress applied to specimens in the course of their isothermal annealing was found to enhance the decay rate of an oxygen solid solution in Cz–Si.